

FORM PTO-1449  INFORMATION DISCLOSURE CITATION IN AN APPLICATION				DOCKET NUMBER SLA786		APPLICATION NUMBER 10/812,591	
				APPLICANT Joshi et al.			
				FILING DATE:		GROUP ART UNIT 2891	

  

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROP.
AKS	6,136,727	10/24/00	Ueno	438	770	12/18/98
AKS	6,437,371	8/20/02	Lipkin et al.	257	77	2/12/01
AKS	6,482,704	11/19/02	Amano et al.	438	285	11/17/00

  

FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

  

OTHER DOCUMENTS	
AKS	"Rapid oxidation of SiC using microwave-discharged O <sub>2</sub> plasma at low temperatures (<300 °C)", M. Satoh, H. Shimada, T. Nakamura, and S. Yanagihara, Japanese Journal of Applied Physics, Vol. 41, pp. L233-L235, 2002.

EXAMINER Asole Kumar Sacha	DATE CONSIDERED 1/13/06
-------------------------------	----------------------------